

MPFF50R12RB R3 1200V 50A IGBT Module

Electrical Features

- Trench/Fieldstop IGBT
- Half-bridge
- Standard package
- Including anti-parallel FWD



Typical Applications

- High Power Converters
- UPS Systems
- Welding Machine

Maximu	m Rated Values						
Symbol	Item	Conditions			Rating		Unit
IGBT							
V _{CES}	Collector-emitter voltage	T _{vj} =25°C			1200		V
V _{GES}	Gate-emitter voltage	-			±20		V
I _C	Collector current,DC	$T_{C}=100^{\circ}C, T_{vj}=175^{\circ}$	°C		50		А
I _{CRM}	Repetitive peak collector current	t _p =1ms			100		А
Ptot	Total power dissipation	$T_{C}=25^{\circ}C, T_{vj}=175^{\circ}C$	$T_{C}=25^{\circ}C, T_{vj}=175^{\circ}C$			579	
Characte	eristics Values						
Symbol	Item	Conditio	ons	Values			Unit
IGBT	IGBT		Min.	Тур.	Max.		
I _{CES}	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$		-	-	1	mA
I _{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$		-	-	250	nA
V _{GE(th)}	Gate-emitter threshold voltage	$I_C=1mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$		5.2	5.7	6.4	
	Collector-emitter saturation voltage	I _C =50A	$T_{vj}=25^{\circ}C$	-	1.9	2.3	v
V _{CEsat}		$V_{GE}=15V$	T _{vj} =125°C	-	2.4	-	v
			T _{vj} =150°C	-	2.4	-	
Cies	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ f=1MHz, $T_{vj}=25^{\circ}C$		-	3.9	-	nF
Cres	Reverse transfer capacitance			-	0.1	-	ШГ
Q _G	Gate charge	V _{GE} =-15V+15V -		0.61	-	uC	

		1	1	1	T		T.
			T _{vj} =25°C	-	69	-	
t _{d(on)}	Turn-on delay time		T _{vj} =125°C	-	63	-	
		_	T _{vj} =150°C	-	62	-	
t _r	Rise time		T _{vj} =25°C	-	54	-	
		V COOV	T_{vj} =125°C	-	51	-	- ns -
		$V_{\rm CC}=600V,$	T_{vj} =150°C	-	49	-	
	Turn-off delay time	$I_{C}=50A,$ $V_{GE}=\pm 15V,$	$T_{vj}=25^{\circ}C$	-	146	-	
$t_{d(off)}$			T_{vj} =125°C	-	158	-	
		$R_{G(on)}=10 \Omega$,	T _{vj} =150°C	-	159	-	
		$- R_{G(off)} = 10 \Omega,$	T _{vj} =25°C	-	159	-	
$t_{\rm f}$	Fall time	di/dt=1220A/µs (T _{vi} =125°C)	T _{vj} =125°C	-	200	-	
		$(1_{vj}-125 \text{ C})$ - du/dt=6765V/µs	T _{vj} =150°C	-	217	-	
		$(T_{vj}=125^{\circ}C)$	T _{vj} =25°C	-	3.58	-	- mJ
Eon	Turn-on energy (per pulse)	$(1_{vj}-125 C)$	T _{vj} =125°C	-	4.67	-	
			T _{vj} =150°C	-	4.99	-	
	Turn-off energy (per pulse)		T _{vj} =25°C	-	1.70	-	
E _{off}			T _{vj} =125°C	-	2.09	-	
			T _{vi} =150°C	-	2.53	-	
R _{thJC}	Thermal resistance, junction to case	per IGBT		-	0.259	-	K/W
R _{thCH}	Thermalresistance, case to heatsink	per IGBT/ λ grease=1W/(m·K)		-	0.159	-	K/W
T _{vjop}	Temperature under switching conditions	-40		-40		150	°C
Diode,				I			
	m Rated Values						
Symbol	Item	Co	nditions		Rat	ting	Unit
V _{RRM}	Repetitive peak reverse voltage	T _{vi} =25°C				00	V
I	Forward current,DC	$T_{\rm C}=100^{\circ}{\rm C}, T_{\rm vi}=175$	°C		25		Α
I _{FRM}	Repetitive peak forward current	t _p =1ms			50		Α
	eristic Values	P			_		
			T _{vj} =25°C	-	1.8	2.45	
$V_{\rm F}$	Continuous forward voltage	$I_F = 25A$	T _{vj} =125°C	-	1.4	_	V
. 1	Continuous for ward vortage	$V_{GE}=0V$	$T_{vj}=150^{\circ}C$	_	1.4	-	
			$T_{vj}=25^{\circ}C$	-	34	-	
I _{RM}	Peak reverse recovery current	$T_{vj}=125$ °C		-	47	-	А
-1111			53	-			
t _{rr}	Reverse recovery time	$V_R=600V$	$T_{vj} = 150^{\circ}C$	_	107	_	
		$I_F = 50A$	$T_{vj} = 125^{\circ}C$	-	232	-	ns
•11		$-di_F/dt=1220A/\mu s$	$T_{vj} = 150^{\circ}C$	-	232	_	115
		(T _{vj} =125°C)	$T_{vj}=150$ C $T_{vj}=25$ °C	_	2.2	_	
Qr	Recovered charge		$T_{vj}=25$ °C	_	4.8	-	μC
×r	Recovered charge		$T_{vj}=123$ C $T_{vj}=150$ °C	-	5.8	-	μυ
			$1_{VJ} = 150 C$	-	5.0	-	1

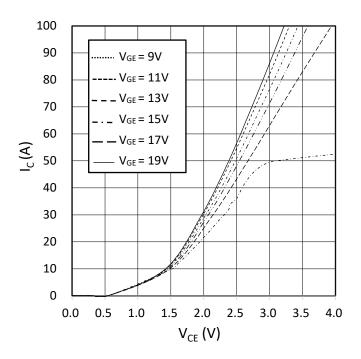
			T _{vj} =25°C	-	0.73	-	
Erec	Reverse recovery energy		T _{vj} =125°C	-	2.02	-	mJ
			T _{vj} =150°C	-	2.48	-	
R _{thJC}	Thermal resistance, junction to case	per diode		-	0.54	-	K/W
R_{thCH}	Thermalresistance, case to heatsink	per diode/ λ grease=1W/(m·K)		-	0.175	-	K/W
T _{vjop}	Temperature under switching conditions			-40		150	°C

Module

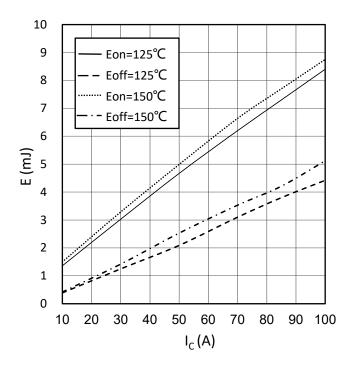
Symbol	Item	Conditions	Rating		,	Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS,f=50Hz,t=1min	2500		V	
-	Material of module baseplate	-		Cu		-
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al ₂ O ₃		-	
T _{stg}	Storage temperature	-	-40~125		°C	
Symbol	Item		Values			Unit
		Conditions	Min.	Тур.	Max.	
М	Mounting torque for module mounting	Screw M6	3.0	-	5.0	Nm
	Terminal connection torque	Screw M5	2.5	-	5.0	Nm
1	Creepage distance	Terminal to terminal	-	23	-	
ds		Terminal to base plate	-	29	-	mm
da	Clearance	Terminal to terminal	-	11	-	
		Terminal to base plate	-	23	-	mm
m	Weight	-	-	150	-	g

output characteristic IGBT, Inverter (typical)

 $I_{C} = f(V_{CE})$ $T_{vj} = 150^{\circ}C$

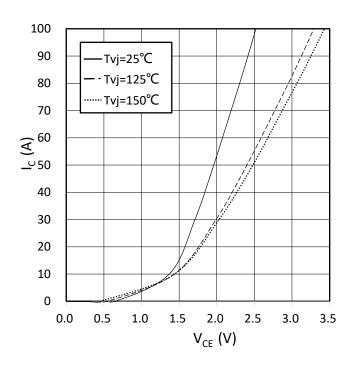


switching losses IGBT,Inverter(typical) $E_{on} = f(I_C), E_{off} = f(I_C)$ $V_{GE} = \pm 15V, R_{Gon} = 10\Omega, R_{Goff} = 10\Omega, V_{CE} = 600V$

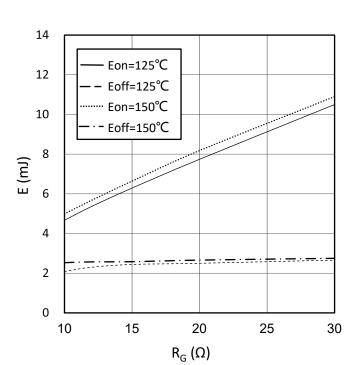


output characteristic IGBT, Inverter (typical)

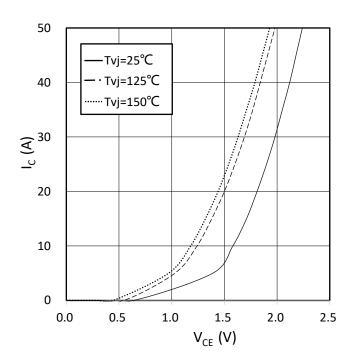
 $I_{C} = f(V_{CE})$ $V_{GE} = 15 V$



switching losses IGBT,Inverter(typical) $E_{on} = f(R_G), E_{off} = f(R_G)$ $V_{GE} = \pm 15V, I_C = 50A, V_{CE} = 600V$

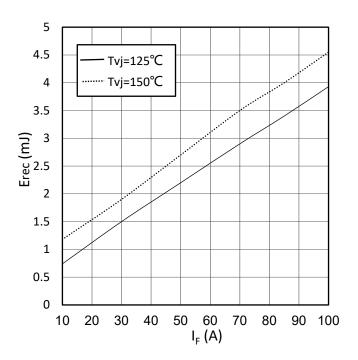


forward characteristic of Diode, Inverter (typical) $I_{\text{F}} = f\left(V_{\text{F}}\right)$

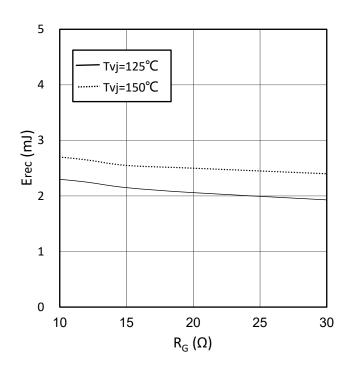


switching losses Diode, Inverter (typical)

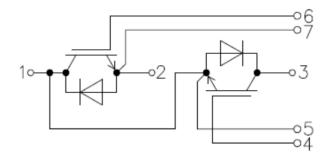
 $E_{rec} = f(I_F)$ R_{Gon}=10 Ω , V_{CE}=600V



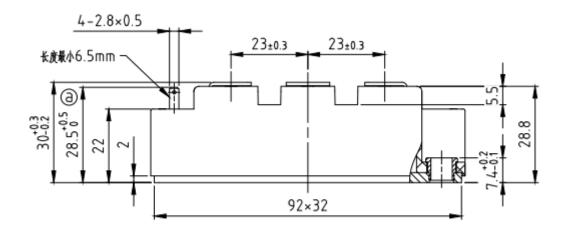
switching losses Diode, Inverter (typical) $E_{rec} = f(R_G)$ $I_F=50A, V_{CE}=600V$

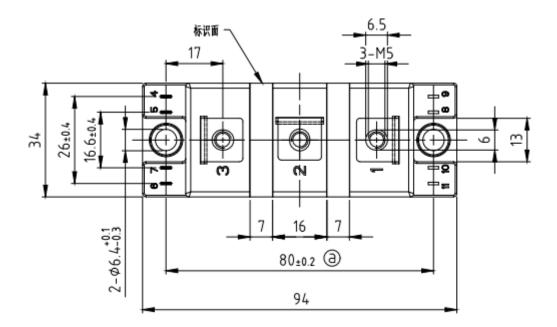


Circuit diagram headline



Package outlines (Unit: mm)





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序号 Item	日期Date	变更记录及描述 Change History Description	版本序号 Rev. item	经办人 Responsibility
1	22/11/14	初版规格书发布,版本为V1.0	2022 11 Ver1.0	梁华文
2	23/2/11	更新热阻、功率,版本为V1.1	2023 02 Ver1.1	梁华文